

GCMX040A120B2B1P

QSiC™ 1200V SiC Half-Bridge Module

Features

- High speed switching SiC MOSFETs
- Reliable body diode
- All parts tested to above 1350V
- Kelvin reference for stable operation
- Press fit terminal connections

Benefits

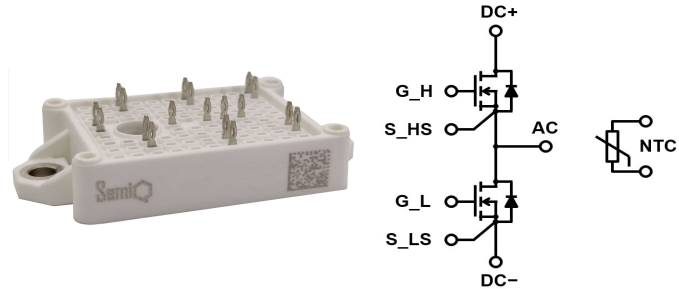
- Low switching losses
- Low junction to case thermal resistance
- Very rugged and easy mounting
- Direct mounting to heatsink (isolated package)

Applications

- Photovoltaic Inverter
- Battery charger
- Energy storage system
- High voltage DC to DC converter

V_{DS}	1200 V
$R_{DS,on}$	38 mΩ
I_D (TC=25°C)	56 A
$T_{J,max}$	175°C

Package



Part #	Package	Marking
GCMX040A120B2B1P	B2	GCMX040A120B2B1P



Absolute Maximum Ratings, at $T_J=25^\circ\text{C}$, unless otherwise specified

Characteristics	Symbol	Conditions	Values	Unit
Drain-Source Voltage	V_{rated}	$V_{GS}=0V$, $I_D=1\mu A$	1200	V
Continuous Drain Current	I_{DS}	$T_C=25^\circ\text{C}$, $V_{GS}=20V$, $T_J=175^\circ\text{C}$	56	A
		$T_C=65^\circ\text{C}$, $V_{GS}=20V$, $T_J=175^\circ\text{C}$	49	
Body Diode Drain Current	I_{SD}	$T_C=25^\circ\text{C}$, $V_{GS}=-5V$, $T_J=175^\circ\text{C}$	66	
Pulsed Drain Current	$I_{DS,pulse}$	$T_C=25^\circ\text{C}$, $V_{GS}=20V$	160	
Gate Source Voltage	V_{GSmax}		-10/25	V
	V_{GSop}	Recommended operational	-5/20	
Power Dissipation	P_{tot}	$T_C=25^\circ\text{C}$	217	W
Operating & Storage Temperature	T_J	Continuous	-40...175	$^\circ\text{C}$
	T_C , $T_{storage}$	Continuous	-40...150	$^\circ\text{C}$

Static Electrical Characteristics, at $T_J=25^\circ\text{C}$, unless otherwise specified

Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=1mA$	1200	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=1200V, V_{GS}=0V$	-	0.1	1	μA
		$V_{DS}=1200V, V_{GS}=0V, T_J=150^\circ\text{C}$	-	1	100	
Gate-Source Leakage Current	I_{GSS+}	$V_{GS}=20V, V_{DS}=0V$	-	10	1000	nA
	I_{GSS-}	$V_{GS}=-5V, V_{DS}=0V$	-	-10	-1000	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=10mA$	1.8	2.9	4	V
		$V_{GS}=V_{DS}, I_D=10mA, T_J=150^\circ\text{C}$	-	2.0	-	
Drain-Source On-Resistance	$R_{DS(on)}^*$	$V_{GS}=20V, I_D=40A$	-	38	52	m Ω
		$V_{GS}=20V, I_D=20A$	-	35	-	
		$V_{GS}=20V, I_D=40A, T_J=150^\circ\text{C}$	-	61	-	
Transconductance	g_{fs}	$V_{DS}=20V, I_D=40A$	-	16.1	-	S
		$V_{DS}=20V, I_D=40A, T_J=150^\circ\text{C}$	-	16.9	-	
Internal Gate Resistance	$R_{G(int)}$	f=1MHz, VAC=25mV, D-S Short	-	1.9	-	Ω

* $R_{DS(on)}$ including package resistance

AC Electrical Characteristics, at $T_J=25^\circ\text{C}$, unless otherwise specified

Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Input Capacitance	C_{ISS}	$V_{GS}=0V$	-	3.2	-	nF
Output Capacitance	C_{OSS}	$V_{DS}=800V$	-	0.19	-	
Reverse Transfer Capacitance	C_{RSS}	f=200kHz	-	0.01	-	
Coss Stored Energy	E_{OSS}^{**}	Vac=25mV	-	69	-	μJ
Turn-On Switching Energy	E_{ON}	$T_J=25^\circ\text{C}$	-	0.52	-	mJ
		$T_J=125^\circ\text{C}$	-	0.71	-	
		$T_J=150^\circ\text{C}$	-	0.76	-	
Turn-Off Switching Energy	E_{OFF}	$T_J=25^\circ\text{C}$	-	0.09	-	
		$T_J=125^\circ\text{C}$	-	0.10	-	
		$T_J=150^\circ\text{C}$	-	0.10	-	
Turn-On Delay Time	$t_{D(on)}$	$V_{DD}=600V, I_{DS}=40A,$ $R_{G(ext)}=8.2\Omega, V_{GS}=-5V/20V,$ $L=273\mu H$	-	19	-	ns
Rise Time	t_R		-	7	-	
Turn-Off Delay Time	$t_{D(off)}$		-	40	-	
Fall Time	t_F		-	16	-	
Total Gate Charge	Q_G	$V_{DD}=800V, I_{DS}=40A$ $V_{GS}=-5/20V$	-	120	-	nC
Gate to Source Charge	Q_{GS}		-	40	-	
Gate to Drain Charge	Q_{GD}		-	32	-	

** E_{OSS} is calculated from C_{OSS} curve

Freewheeling Diode Characteristics, at $T_J=25^\circ\text{C}$, unless otherwise specified

Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Diode Forward Voltage	V_{SD}	$V_{GS}=-5\text{V}$, $I_S=40\text{A}$	-	3.4	-	V
		$V_{GS}=-5\text{V}$, $I_S=40\text{A}$, $T_J=150^\circ\text{C}$	-	3.0	-	
Reverse Recovery Time	t_{RR}	$T_J=25^\circ\text{C}$ $I_S=40\text{A}$, $V_R=600\text{V}$, $V_{GS}=-5\text{V}$, $di/dt=9.6\text{A/ns}$	-	12	-	ns
Reverse Recovery Charge	Q_{RR}		-	536	-	nC
Peak Reverse Recovery Current	I_{RRM}		-	81	-	A
Reverse Recovery Energy	E_{RR}	$T_J=25^\circ\text{C}$	-	0.11	-	mJ
		$T_J=125^\circ\text{C}$	-	0.29	-	
		$T_J=150^\circ\text{C}$ $R_{G(\text{ext})} = 8.2\Omega$	-	0.35	-	

Thermal and Package Characteristics, at $T_J=25^\circ\text{C}$, unless otherwise specified

Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal resistance, junction-case	R_{thJC}		-	0.61	0.69	$^\circ\text{C/W}$
Mounting torque	M_d	M4-0.7 screws	-	2.00	2.3	N-m
Press fit pin PCB end hole diameter			0.99	-	1.09	mm
Press fit pin PCB hole drill diameter			1.12	1.15	-	mm
Press fit pin PCB hole copper thickness			25	-	50	μm
Package weight	W_t		-	21	-	g
Isolation voltage	V_{ISOL}	50/60 Hz, 1 min	3000	-	-	V

NTC Characteristics, at $T_J=25^\circ\text{C}$, unless otherwise specified

Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Rated resistance	R_{NTC}	$T_{NTC} = 25^\circ\text{C}$	-	5.0	-	k Ω
Resistance tolerance	$\Delta R/R$		-5	-	5	%
Beta Value ($T_2 = 50^\circ\text{C}$)	$\beta_{25/50}$		-	3380	-	k
Beta Value ($T_2 = 80^\circ\text{C}$)	$\beta_{25/80}$		-	3440	-	k
Power dissipation	P_{MAX}	$T_{NTC} = 25^\circ\text{C}$	-	-	50	mW

Typical Performance

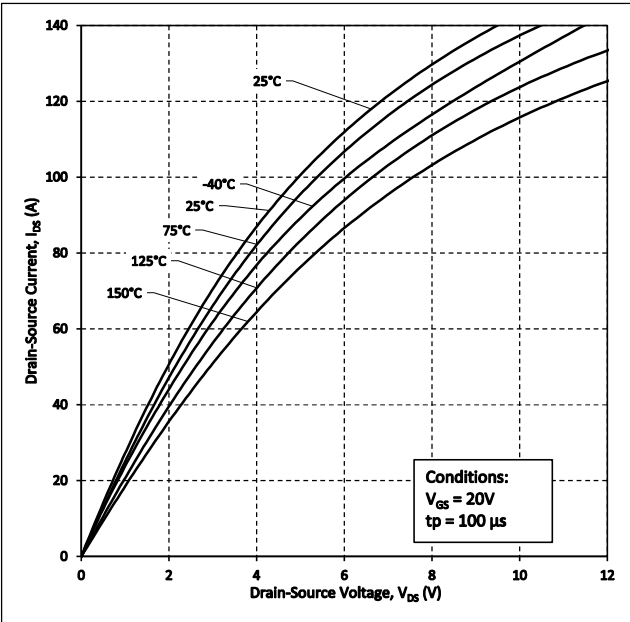


Figure 1. Output Characteristics for Various Temperatures

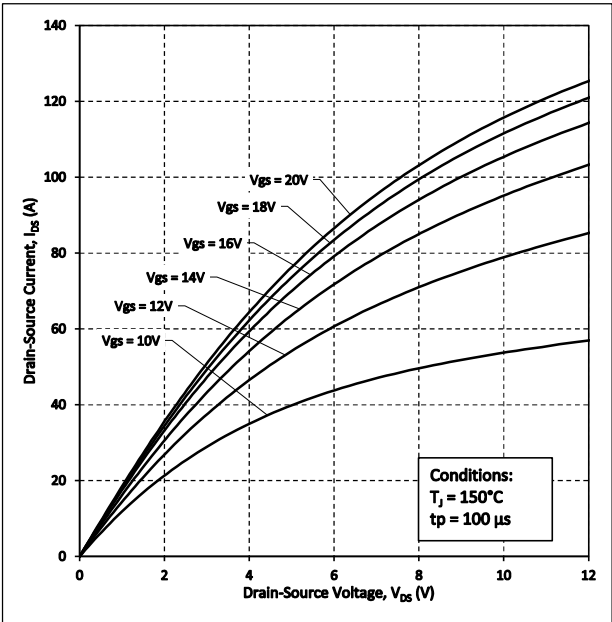


Figure 2. Output Characteristics $T_J = 150^\circ C$

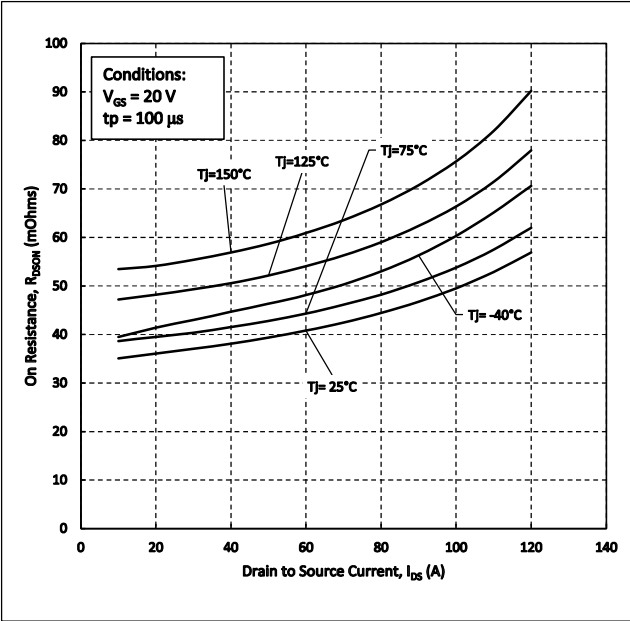


Figure 3. On-Resistance vs. Drain Current For Various Temperatures

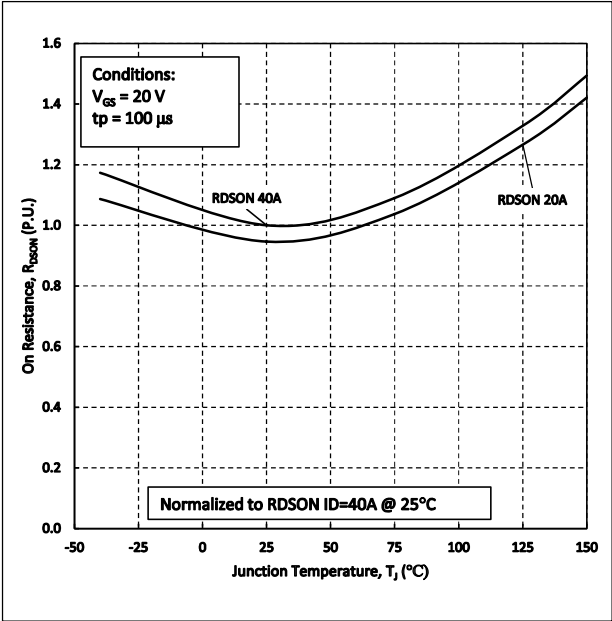


Figure 4. Normalized On-Resistance vs. Temperature

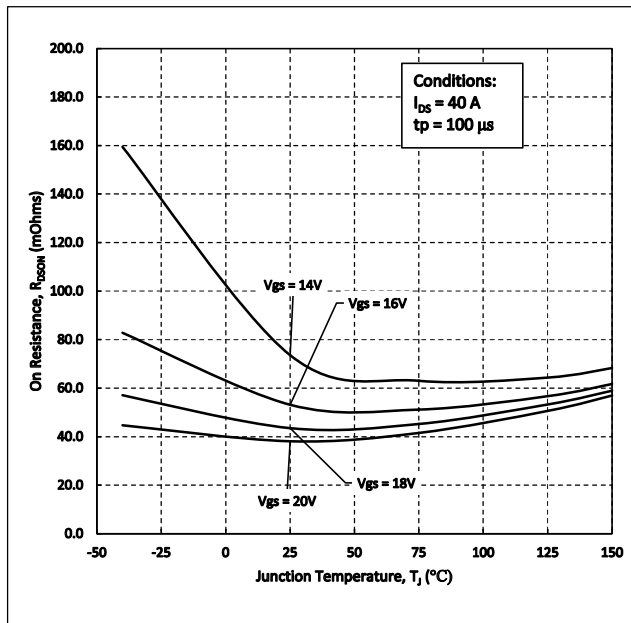


Figure 5. On-Resistance vs. Temperature For Various Gate Voltages

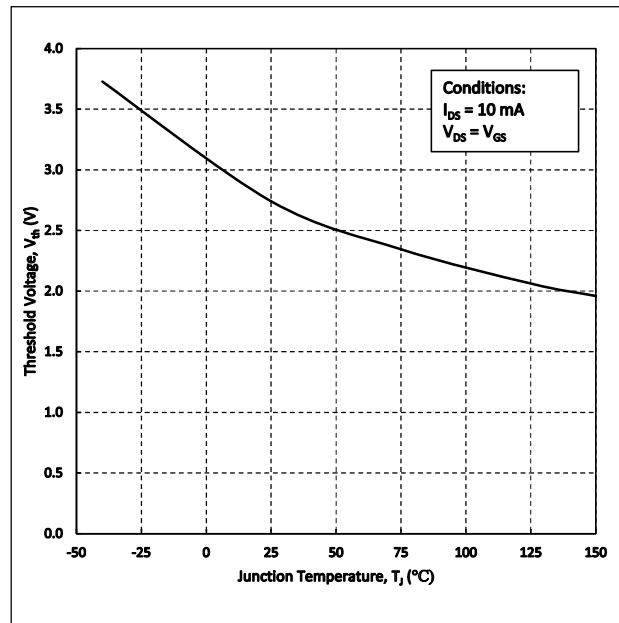


Figure 6. Threshold Voltage vs. Temperature

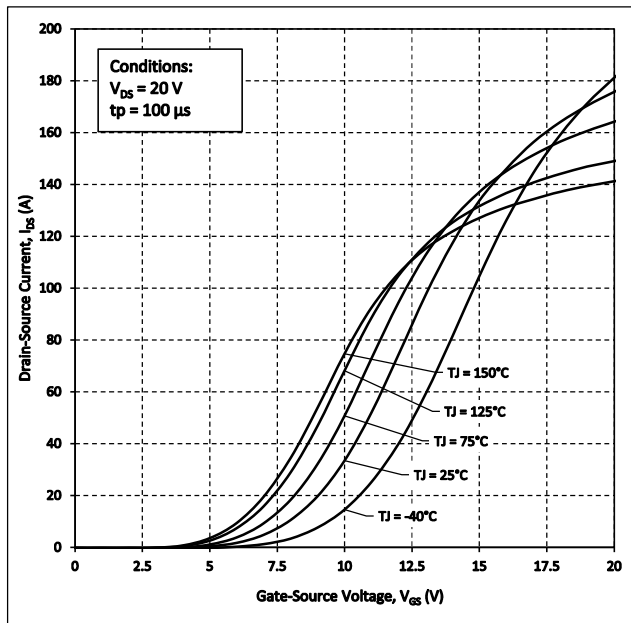


Figure 7. Transfer Characteristic for Various Junction Temperatures

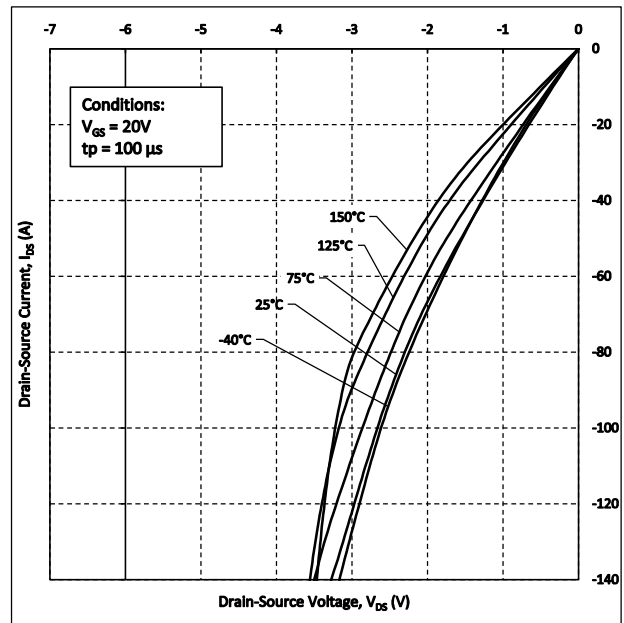


Figure 8. 3rd Quadrant Characteristics at $V_{GS} = 20V$

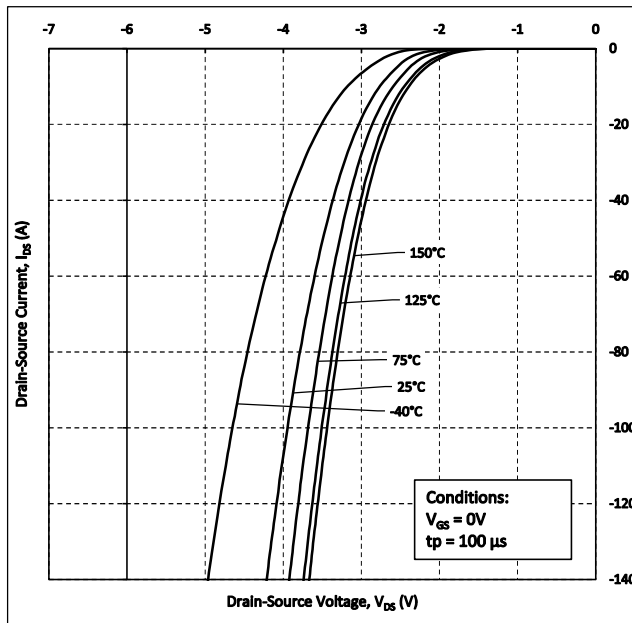


Figure 9. Freewheeling Diode Characteristics at $V_{GS} = 0V$

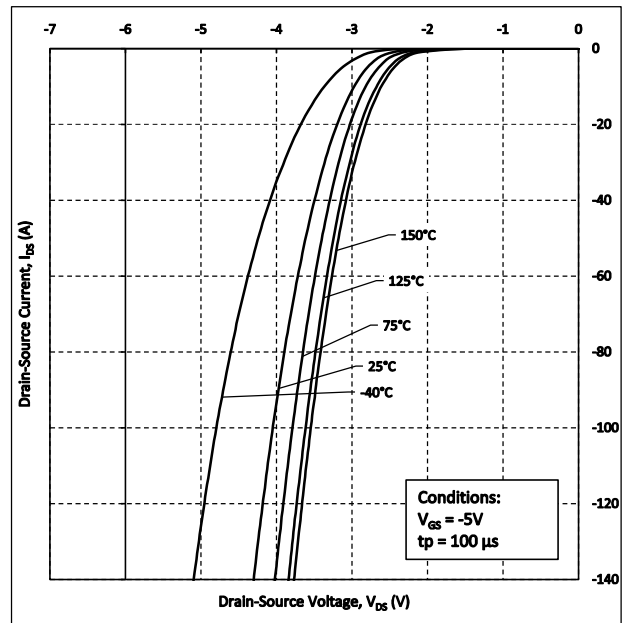


Figure 10. Freewheeling Diode Characteristics at $V_{GS} = -5V$

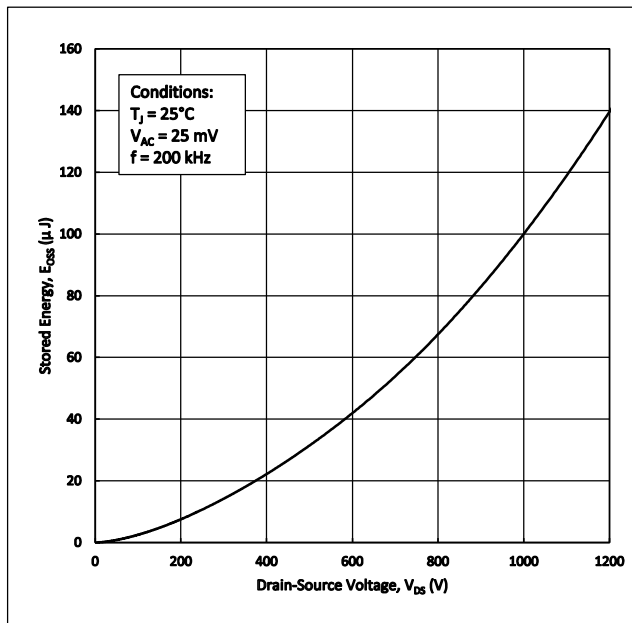


Figure 11. Output Capacitor Stored Energy

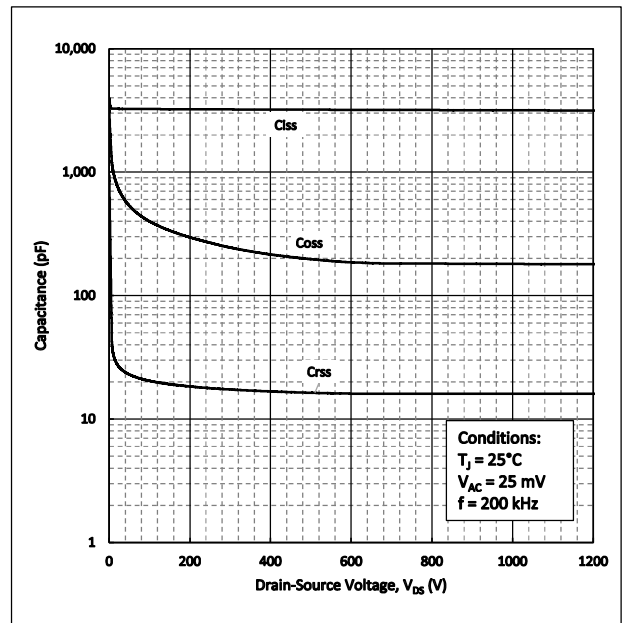


Figure 12. Capacitance vs. Drain-Source Voltage

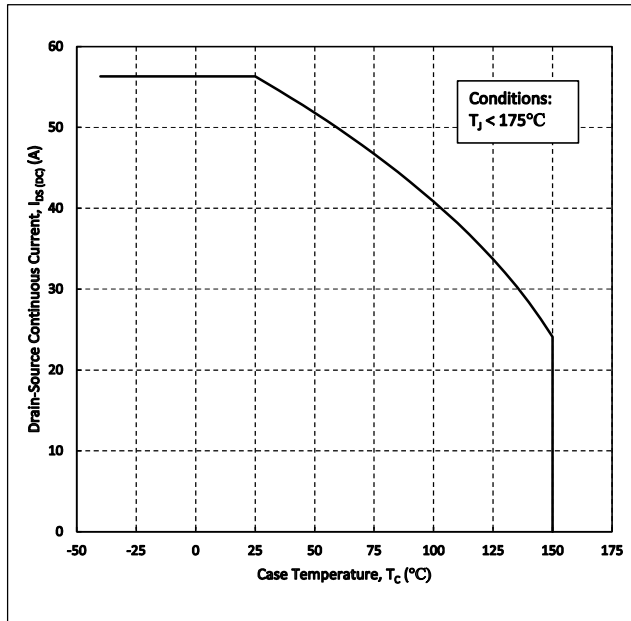


Figure 13. Continuous Drain Current Derating vs. Case Temperature

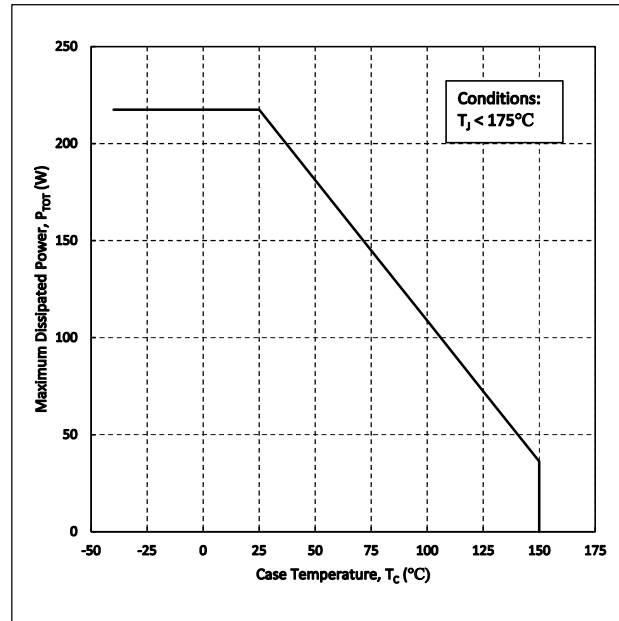


Figure 14. Maximum Power Dissipation Derating vs. Case Temperature

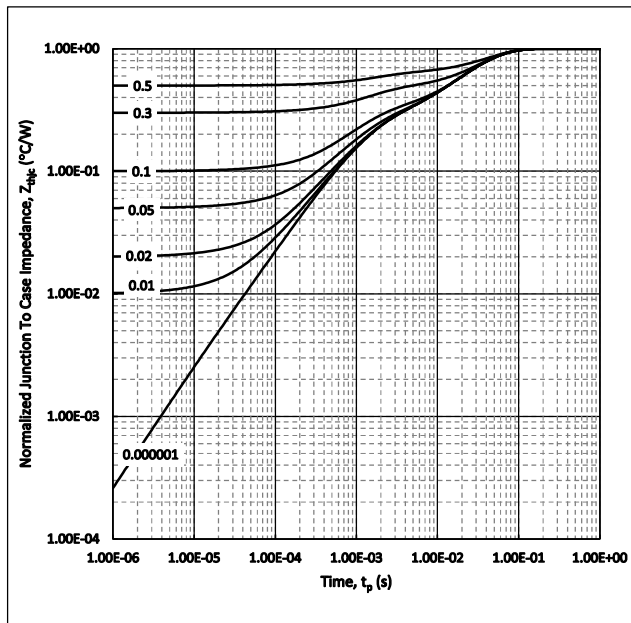


Figure 15. Transient Thermal impedance (Junction to Case)

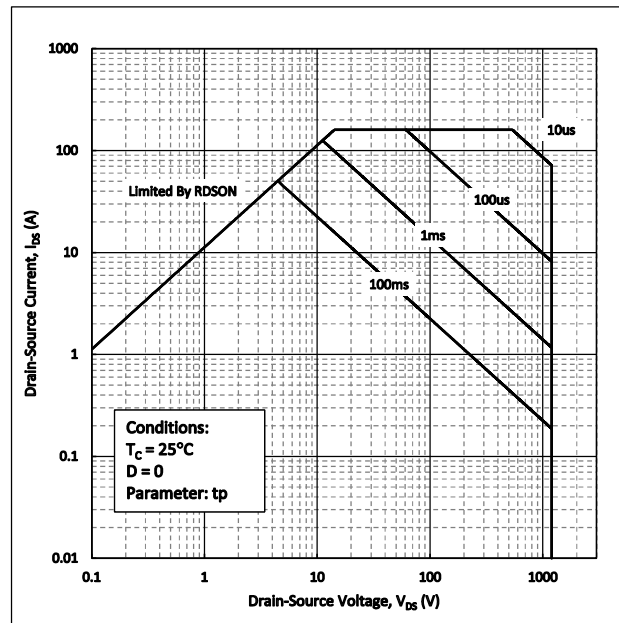


Figure 16. Safe Operating Area

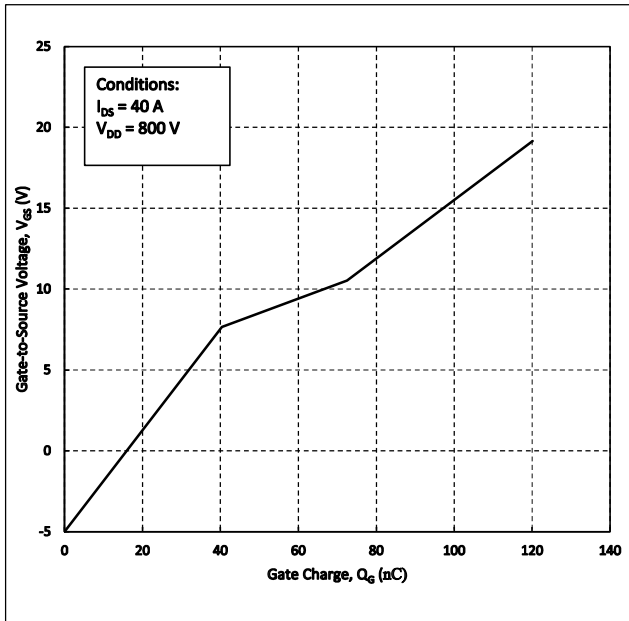


Figure 17. Gate Charge Characteristics

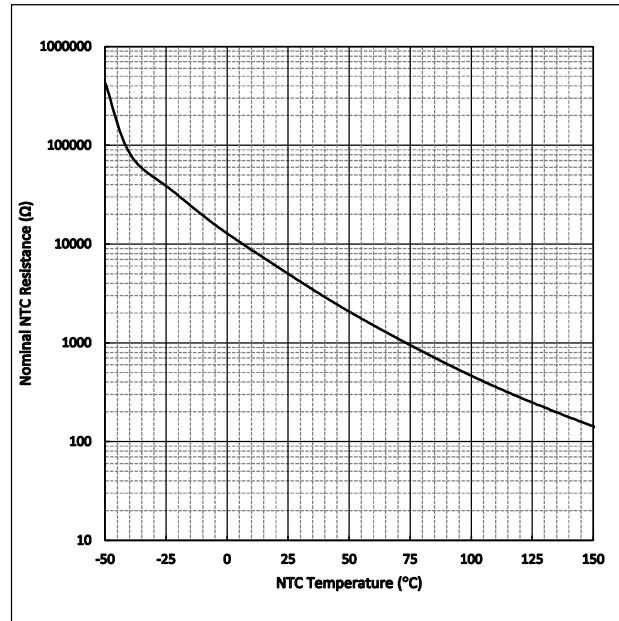


Figure 18. Nominal NTC Resistance vs. Temperature

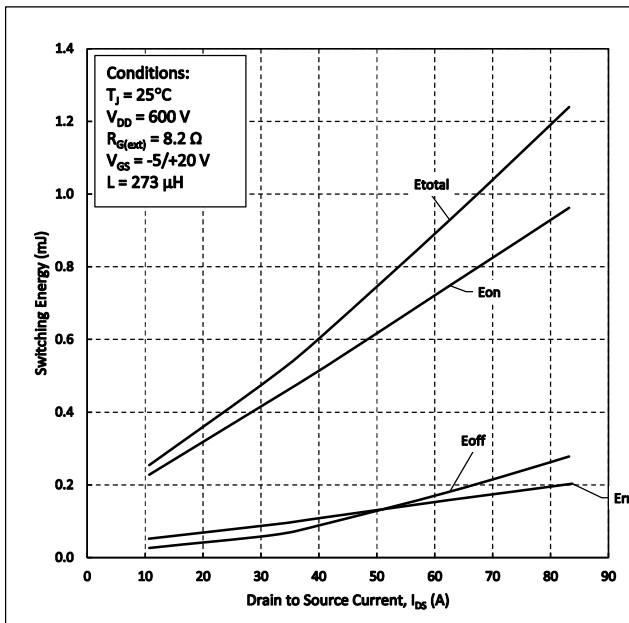


Figure 19. Clamped Inductive Switching Energy vs. Drain Current (600V)

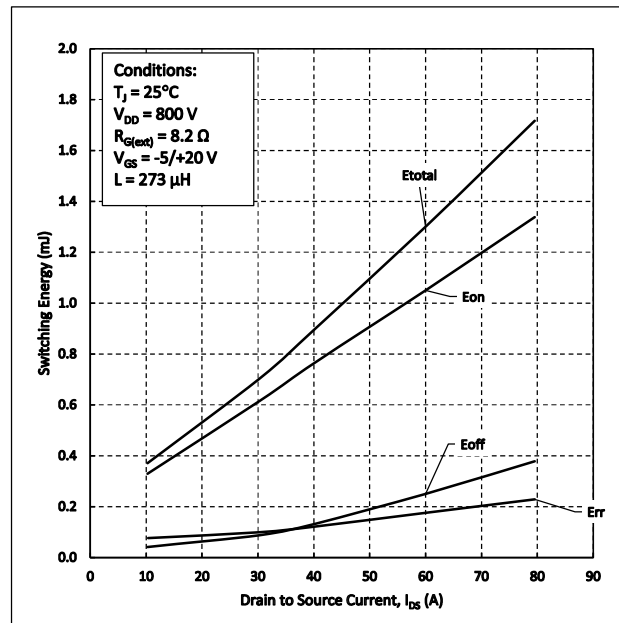


Figure 20. Clamped Inductive Switching Energy vs. Drain Current (800V)

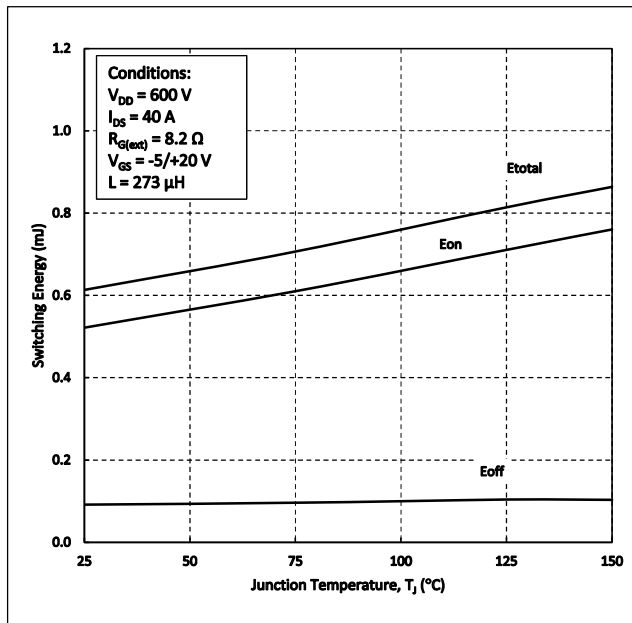


Figure 21. Clamped Inductive Switching Energy vs. Temperature

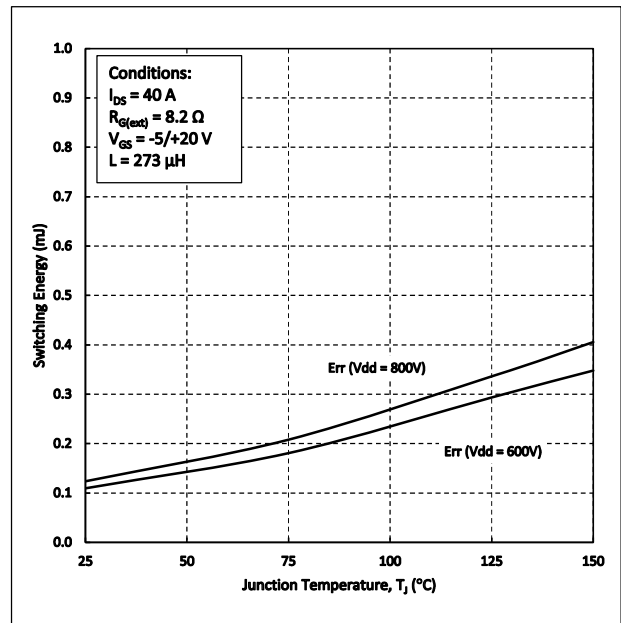


Figure 22. Reverse Recovery Energy vs. Temperature

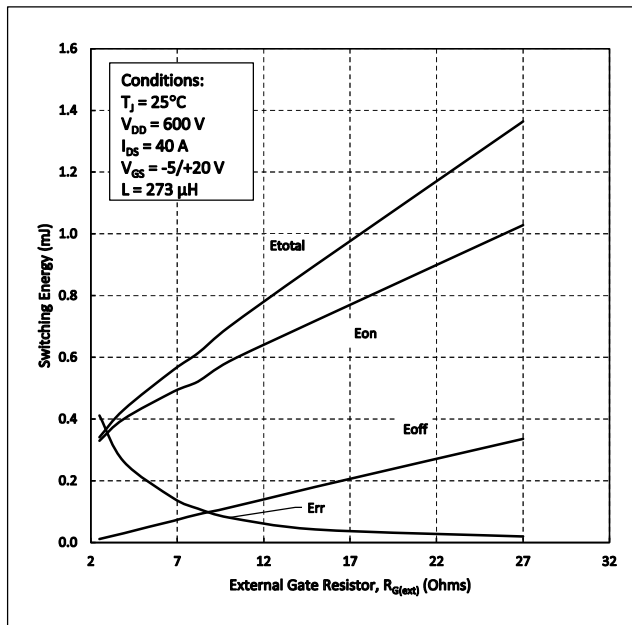


Figure 23. Clamped Inductive Switching Energy vs. $R_{G(ext)}$

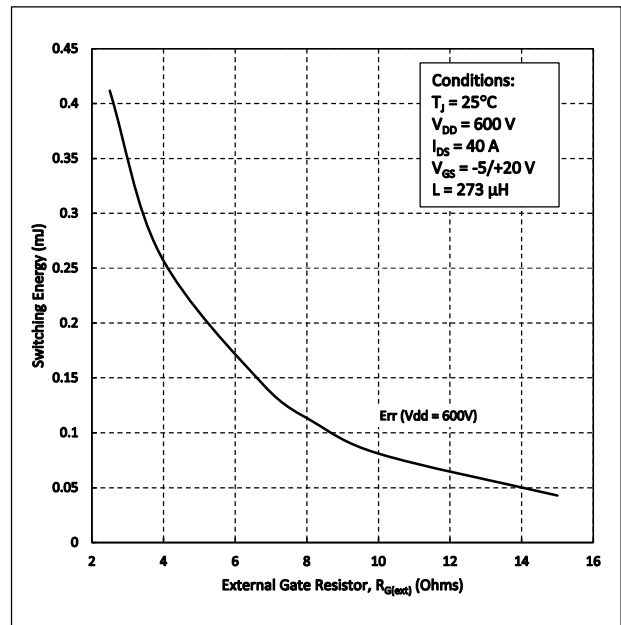


Figure 24. Reverse Recovery Energy vs. $R_{G(ext)}$

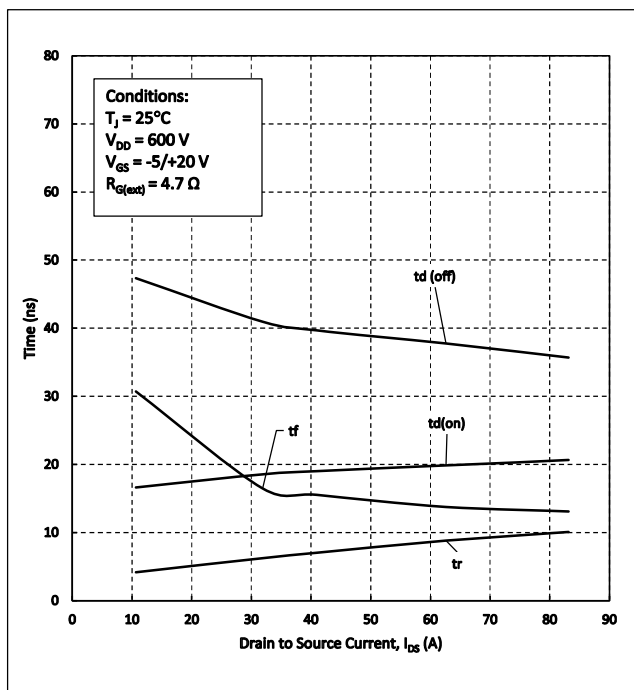


Figure 25. Switching Times vs. Drain Current

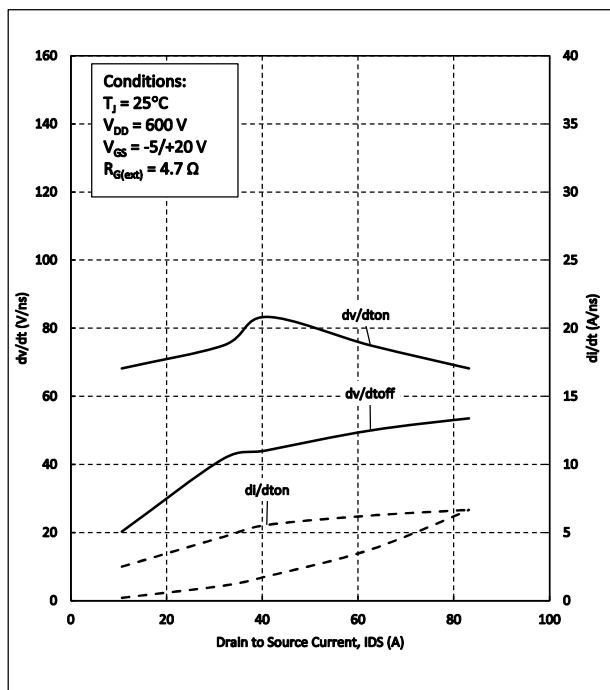


Figure 26. dv/dt and di/dt vs. Source Current

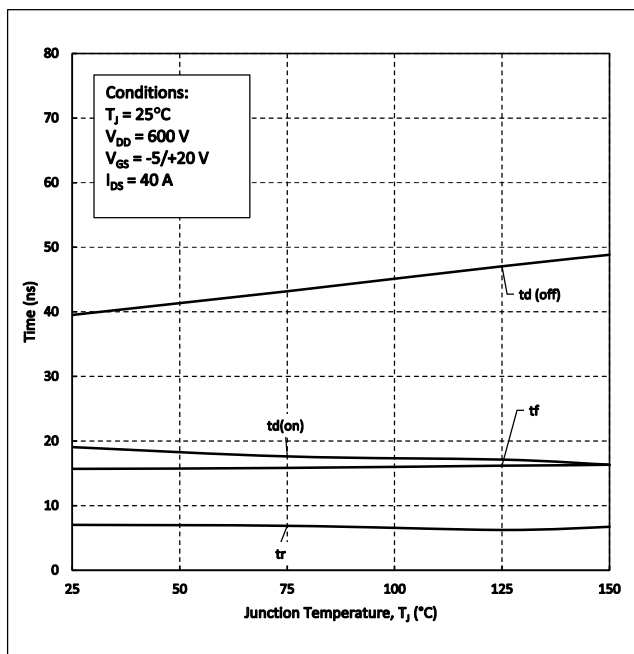


Figure 27. Switching Times vs. Temperature

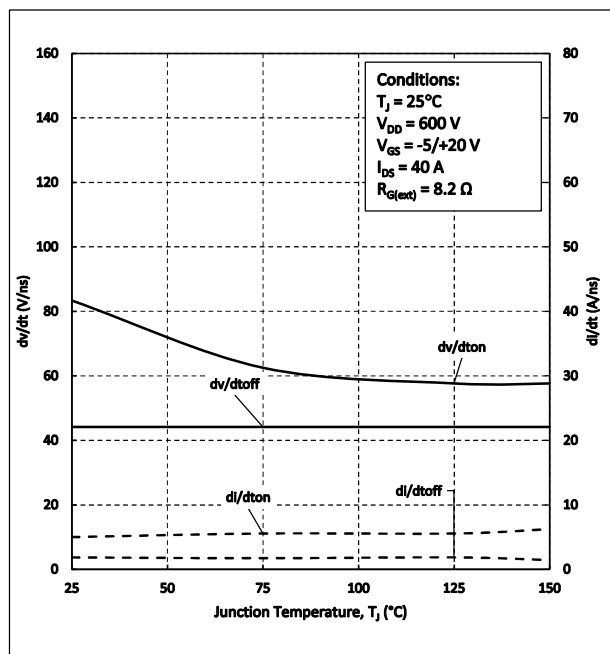


Figure 28. dv/dt and di/dt vs. Temperature

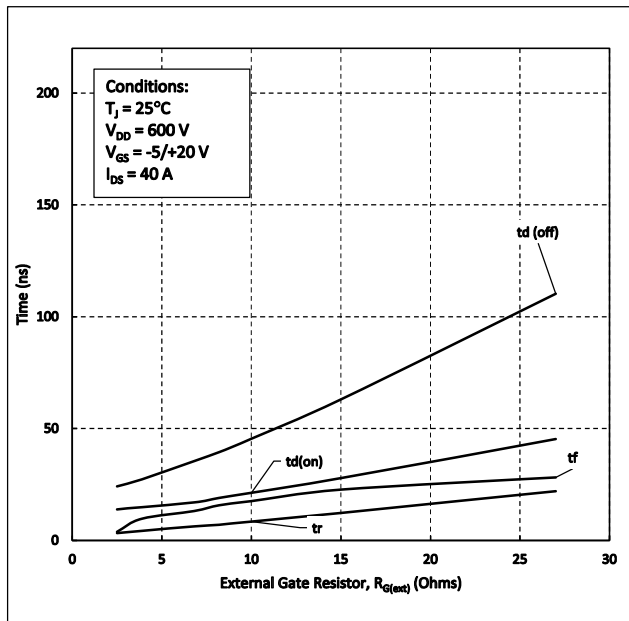


Figure 29. Switching Times vs. $R_{G(ext)}$

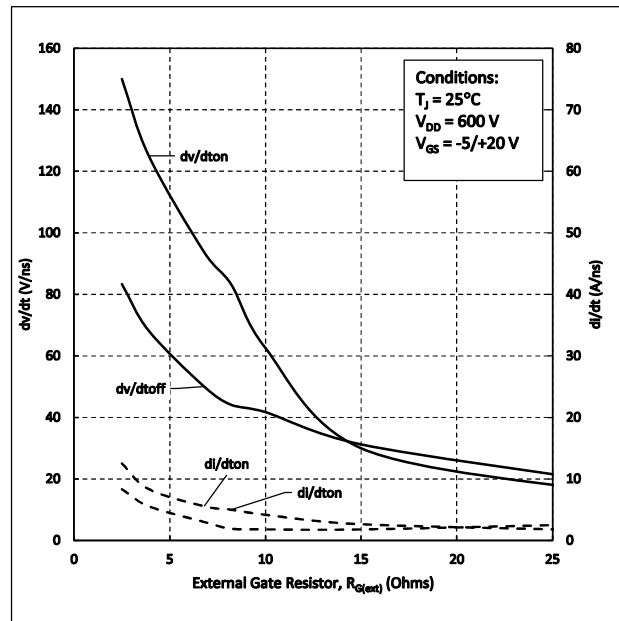


Figure 30. dv/dt and di/dt vs. $R_{G(ext)}$

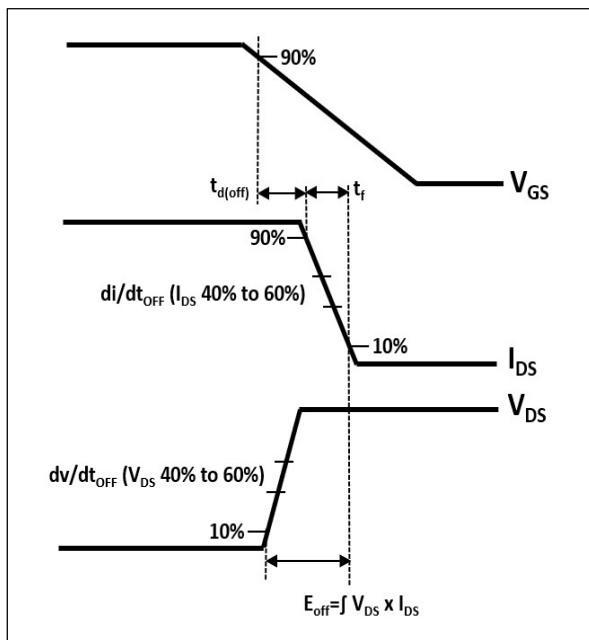


Figure 31. Turn-off Transient Definitions

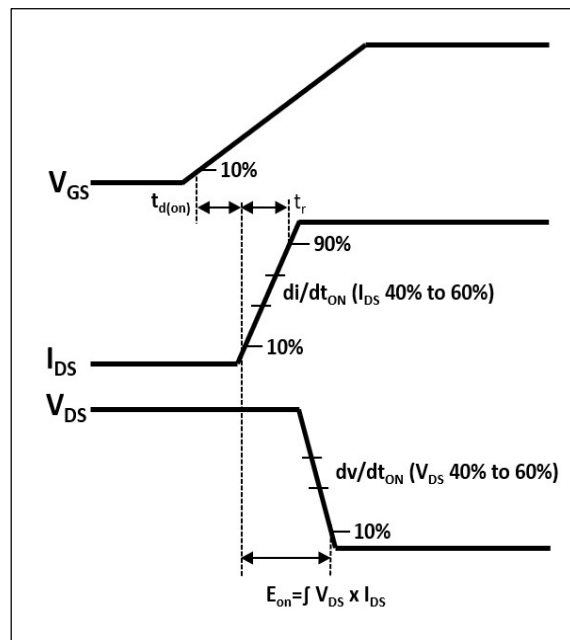


Figure 32. Turn-on Transient Definitions

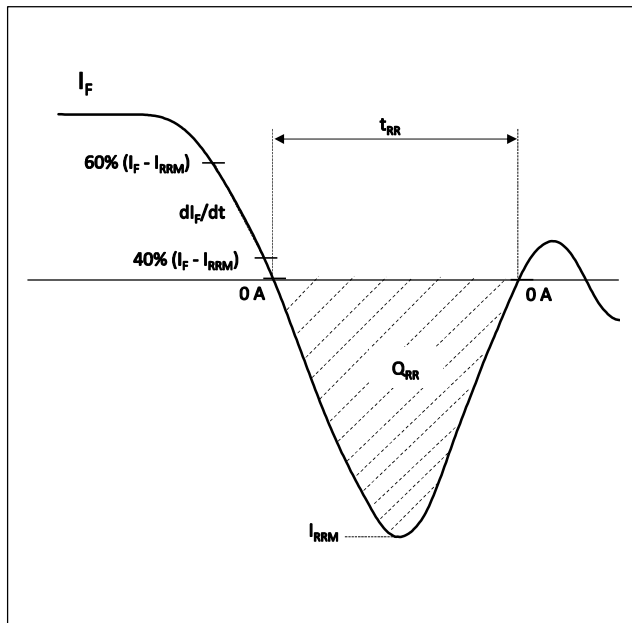
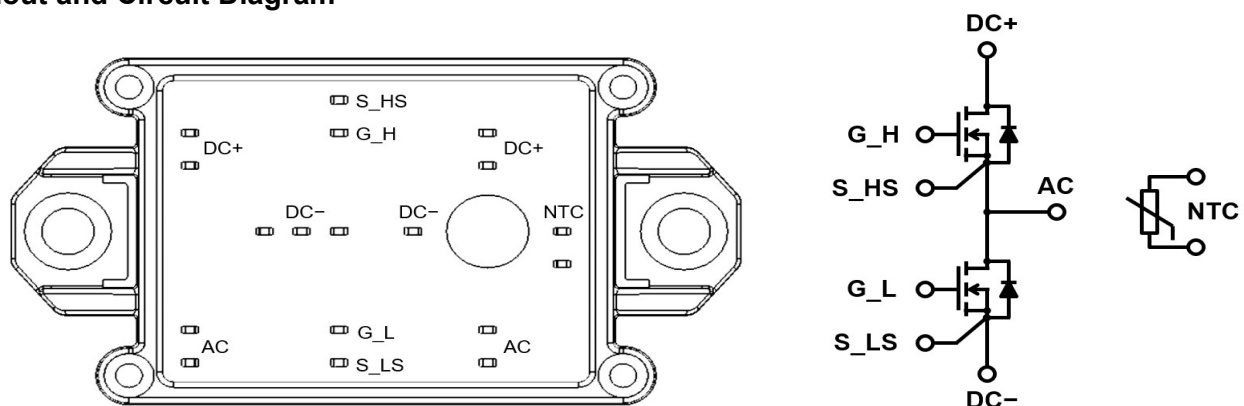


Figure 33. Reverse Recovery Definitions

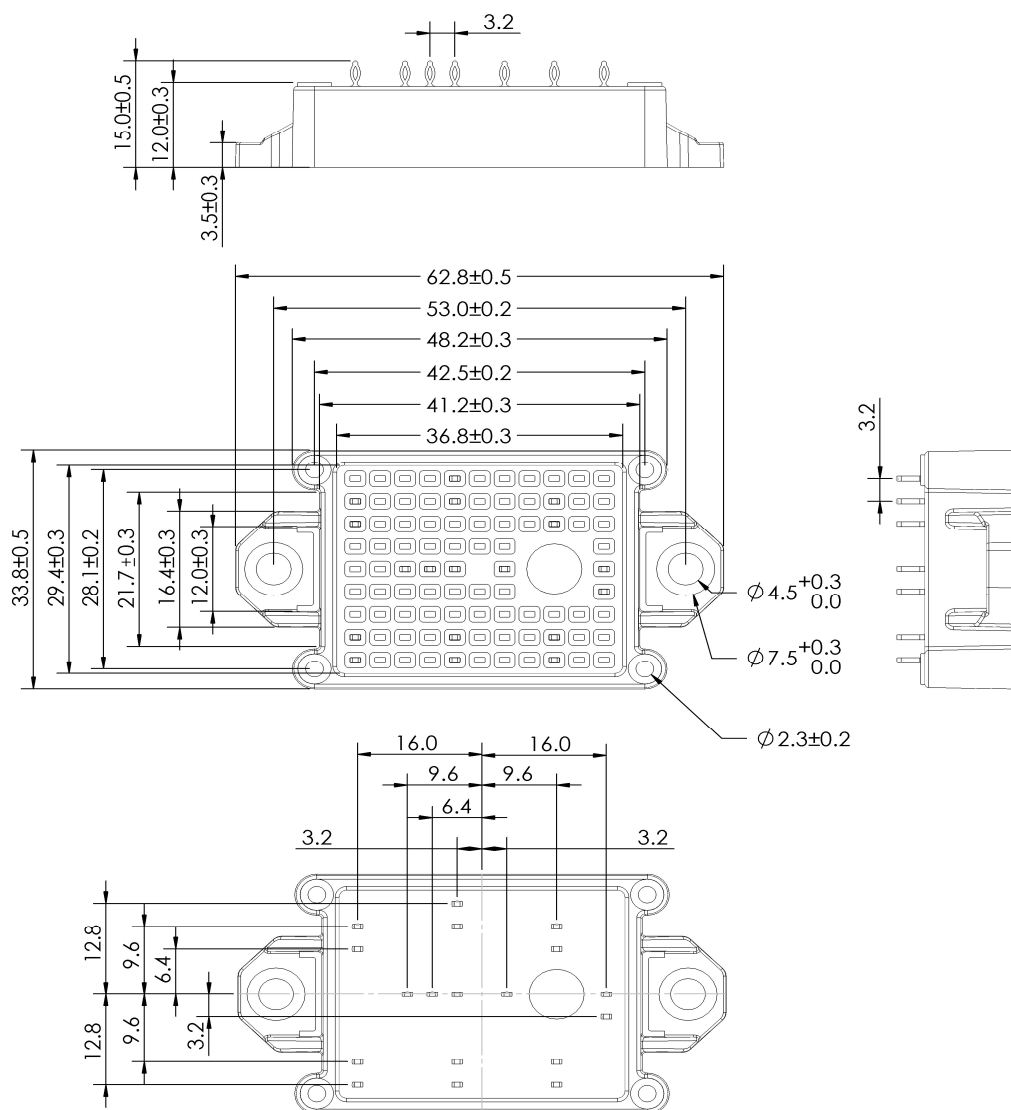
QSiC™ 1200V SiC Half-Bridge Module

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Pinout and Circuit Diagram



Package Dimensions (mm) for B2



Revision History		
Date	Revision	Notes
12/19/2024	1.0	Initial release

Notes

RoHS Compliance

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS2), as implemented March, 2013. RoHS Declarations for this product can be obtained from the Product Documentation sections of www.SemiQ.com.

REACH Compliance

REACH substances of high concern (SVHC) information is available for this product. Since the European Chemicals Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact our office at SemiQ Headquarters in Lake Forest, California to insure you get the most up-to-date REACH SVHC Declaration. REACH banned substance information (REACH Article 67) is also available upon request.

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